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10/26/01  
mccarthy

PATENT  
Attorney Docket No. 401308

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of:

TAKAHIRO OHNAKADO

Application No.: Unassigned

Art Unit: Unassigned

Filed: July 25, 2001

Examiner: Unassigned

For:  
SI-MOS HIGH-  
FREQUENCY  
SEMICONDUCTOR  
DEVICE AND THE  
MANUFACTURING  
METHOD OF THE SAME

**PRELIMINARY AMENDMENT**

Commissioner for Patents  
Washington, D. C. 20231

Dear Sir:

Prior to the examination of the above-identified patent application, please enter the following amendments and consider the following remarks.

**IN THE SPECIFICATION**

Replace the paragraph beginning at page 1, line 2, with:

A1      The present invention relates to a high-frequency semiconductor device employing an Si-MOS transistor, and especially relates to achievement of a reliable and sophisticated high-frequency semiconductor device having high ESD (Electro Static Discharge) resistance.